A universal method for calculating and extracting the LF and RF noise behavior of nonlinear devices

R. Follmann, J. Berben, D. Köther, P. Waldow, J. Borkes and I. Wolff
Institut für Mobil- und Satellitenfunktechnik IMST GmbH,
D–47475 Kamp-Lintfort, Germany, e-mail follmann@imst.de

Abstract—In this paper an efficient method for calculating the noise behavior of active devices is described. This method offers a general solution for a large variety of transistor and other devices. The method can easily be implemented in any extraction and simulation software and allows determination of LF as well as RF noise behavior. The functionality is demonstrated on a nonlinear FET model [1], [2]. Furthermore, verifications with HP series IV/ADS [3] are given for different devices.

I. Introduction

The design of many circuits requires the extraction and the simulation of noise parameters for quite different noisy elements like FETs, BJTs or HBTs. In the past, several papers have been presented describing an extraction process for different noise models [4], [5]. Many of these methods are limited to special kinds of active devices. Most CAD circuit simulation software does not allow the extraction of parameters, although it has implemented functions to calculate noise. For noise extraction exactly these functions must be known in order to fit e.g. noise function coefficients to measurements during an optimization process. Therefore, in this paper we present an efficient method for calculating noise behavior of any device. Our proposed method is based upon the Y-matrix of any equivalent circuit and a matrix containing the noise sources for that equivalent circuit. With that knowledge both LF as well as RF noise behavior can be extracted and calculated. We describe how our proposed method can be used for extracting and simulating noisy circuits. The method can be applied to any extraction and simulation software.

II. Transforming noise sources

When simulating a circuit, noisy n-ports must be transformed into a non-noisy n-port and associated noise sources at outer ports. Fig. 1 shows an example of transforming noisy networks to non-noisy ones including a current source and a voltage source at the output for the 2-port. Using the transformation matrix

\[ [T]^{(y \rightarrow o)} = \begin{bmatrix} 0 & 1 \frac{1}{2kT} \\ 1 & \frac{1}{2kT} \end{bmatrix}, \]

the noise matrix of currents can be calculated in a form using equation (2):

\[ \begin{bmatrix} \psi_{i}^{(o)} \\ \psi_{0}^{(o)} \\ \psi_{i}^{(o)} \\ \psi_{0}^{(o)} \end{bmatrix} = [T]^{(y \rightarrow o)} \begin{bmatrix} \psi_{i}^{(y)} \\ \psi_{0}^{(y)} \\ \psi_{i}^{(y)} \\ \psi_{0}^{(y)} \end{bmatrix}, \]

whereby the indices i and o describe input and output ports. For calculating noise power, the column vectors are multiplied with the conjugated row vectors of the noise source matrix and end up by division with \( 4kT\Delta f \) in the wellknown correlation matrix

\[ [C]^{(o)} = \frac{1}{4kT\Delta f} \begin{bmatrix} \psi_{i}^{(o)} \\ \psi_{0}^{(o)} \\ \psi_{i}^{(o)} \\ \psi_{0}^{(o)} \end{bmatrix} \begin{bmatrix} \psi_{i}^{(o)*} \\ \psi_{0}^{(o)*} \\ \psi_{i}^{(o)*} \\ \psi_{0}^{(o)*} \end{bmatrix}. \]

III. Noise analysis

There are different ways of calculating noise. One way is the division of a circuit into different sub-2-ports with noise sources, that have been transformed as described above. Noise behavior for each 2-port can be easily calculated e.g. using node analysis. The separately calculated 2-ports can be combined using the transformation matrices.
In this paper a different approach is used. Taking into account the Tellegen theorem, current and voltage sources can be transformed to the outer ports of a network \( N \). To do this, the adjuncted network \( \bar{N} \) is required, which has a definite reversible relation to the network \( N \). The \( Y \)-matrix of the adjuncted network \( \bar{N} \) represents the transposed \( Y \)-matrix of the network \( N \) as well. With that knowledge, a current source e.g. can be transformed to the outer ports using just one node analysis for the adjuncted network and \( k - 1 \) analysis for the network \( N \), whereby \( k \) gives the number of nodes in the network \( N \). Using a circuitry as shown in fig. 2, the current transformation function \( \alpha \) is equal to the negative voltage transformation function of the adjuncted network \( \bar{N} \):

\[
\alpha_{i,jk} = \frac{i_j}{i_{jk}} = \frac{-v_{jk}}{v_q}.
\] (4)

This fact can be used for calculating noise behavior as shown for an example in the next section.

**IV. CALCULATING FET NOISE**

The applicability of the Tellegen theorem is shown for a FET equivalent circuit (fig. 3). The circuitry takes care of different noise mechanisms in FETs, like resistive noise and channel noise. Furthermore, \( 1/f \) noise is taken into account. The ten nodes of the equivalent circuit are numbered in order to determine the \( 10 \times 10 \) \( Y \)-matrix. In correspondence with the \( Y \)-matrix, a \( 10 \times 10 \) noise matrix can be defined. The position of noise sources in that matrix is given by the node numbers at the end of the noise source. The direction of the current is defined in the way, that at matrix entry \( i_{jk} \) the noise current in the equivalent circuits flows from node \( j \) into the direction of node \( k \). All noise current sources have only positive entries. The factor \( \sqrt{4kTf} \) is placed outside the brackets. For the presented equivalent circuit the noise current matrix is given to

\[
[i_N] = \sqrt{4kTf} \Delta f \cdot \begin{pmatrix}
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 & 0 \\
\end{pmatrix}
\] (5)

with the resistive noise

\[
i_{5,8} = \sqrt{\frac{T}{r_1}},
\]
\[
i_{5,9} = \sqrt{\frac{1}{g_{DS}}},
\]
\[
i_{6,3} = \sqrt{\frac{T}{R_G}},
\]
\[
i_{7,4} = \sqrt{\frac{T}{R_D}},
\]
\[
i_{7,5} = \sqrt{g_{m}},
\]
\[
i_{10,5} = \sqrt{\frac{T}{R_S}}.
\]

including the channel noise

\[
g_v = \frac{T_{\text{sim}}}{T_0} \frac{2}{3} g_m + k_f \frac{L_n f}{\sqrt{4kT_0}}.
\] (6)

The next calculation steps are converting the \( Y \)-matrix into an \( Z \)-matrix, and re-calculating the \( 2 \times 2 \) \( Y \)-matrix because of the examined 2-port and computing the transposed \( Y \)-matrix

\[
[y_f] = [y]^T.
\] (7)

The adjuncted network shown in fig. 4 is used in order to calculate a voltage transformation function. The volt-
Now, the noise figure can be calculated to

\[ 1 + \frac{\sum_{j=2}^{11} T_{ij} y_{jk} v_{jk}}{v_{q}}. \]

The result delivers a voltage transformation factor, that is equal to the negative current transformation factor. Now, for each noise source the influence at the input and output port of the example 2-port can be calculated. Taking care of the correlation of the noise sources, the influences of the single noise sources can be added to one single noise source at the input as well as the output. At this point a noise free 2-port with two outer noise current sources in Y representation has been determined. With the two noise sources, the correlation matrix can be calculated as described in equation (11). With the help of the transformation matrix \( T^{(y \rightarrow \alpha)} \), the correlation matrix can be changed into the following representation:

\[ \begin{bmatrix} i_{Q_1} \\ i_{Q_{10}} \end{bmatrix} = \begin{bmatrix} y_{T_{11}} & \cdots & y_{T_{110}} \\ \vdots & \ddots & \vdots \\ y_{T_{101}} & \cdots & y_{T_{1010}} \end{bmatrix} \begin{bmatrix} v_{1} \\ \vdots \\ v_{10} \end{bmatrix}. \]

Using the Gauß algorithm, the equation system containing the transposed Y-matrix \( [\Sigma_T] \) can be solved for the voltages:

\[ \begin{bmatrix} i_{Q_1} \\ i_{Q_{10}} \end{bmatrix} = \begin{bmatrix} y_{T_{21,1}} \\ \vdots \\ y_{T_{21,10}} \end{bmatrix} \begin{bmatrix} v_{1} \\ \vdots \\ v_{10} \end{bmatrix}. \]
the same device can be seen for the noise figure at a bias point of $V_{GS} = 0$ V and $V_{DS} = 2$ V. Again, both results are in excellent agreement. The comparison with measurements can be seen in the next two plots (fig. 7 and fig. 8). The same proposed algorithm was used to extract parameters for the $1/f$ noise as described in equation (16)

$$i_f^2 = k_f \frac{P_{1/f}}{f^b} \Delta f$$

(16)

for a 4-finger 50 $\mu$m HEMT device at a bias point of $V_{GS} = 0$ V and $V_{DS} = 1.5$ V. The extracted parameters are $k_f = 1.3 \times 10^{-12}$, $a_f = 0.9$ and $b = 1.05$. Fig. 8 shows the comparison of the simulated and measured noise figure for a 4-finger 40 $\mu$m HEMT at a bias point of $V_{GS} = -0.2$ V and $V_{DS} = 2$ V. All simulations are in excellent agreement with measurements.

**VI. Conclusions**

In our paper an effective method for calculating both LF as well as RF noise of active devices has been demonstrated. The method was compared with the one used by HP-EEsof libra series IV circuit simulation software. It has been shown that both methods lead to nearly the same results. Furthermore, the method we used can easily be applied to any extraction software in order to extract e.g. coefficients for the $1/f$ noise behavior. Also, simulation results in excellent agreement to measurements have been shown.

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**REFERENCES**


Rüdiger Follmann was born in Prüm, Germany, in 1968. He studied electrical engineering at the Technical University of Aachen and received the Dipl.-Ing. degree in 1995. Since 1995 he has been with the Institute of Mobile and Satellite Communication Techniques (IMST). In 1998 he received the doctoral degree from the University of Duisburg, Germany. Since 1999 he has been head of the section "Integrated Communication Circuits" (ICC). His main interests are nonlinear device modeling and MMIC design.

Jörg Berben was born in Duisburg, Germany, in 1969. He studied electrical engineering at the FH Niederrhein and received the Dipl.-Ing. degree in 1999. Since then he has been with the Institute of Mobile and Satellite Communication Techniques (IMST). His main interests are also nonlinear device modeling and MMIC design.
Dietmar Köther was born in 1958 in Duisburg, Germany. He received the electrical engineering degree (MSc) from the University - GH - Duisburg in 1984. From 1984 to 1988 he worked at the Department of Electrical Engineering at the University - GH - Duisburg on the DFG project "Reciprocal and non-reciprocal image guide elements utilizing premagnetized ferrits". In 1989 he got the PhD degree. From 1989 to 1992 he worked for ArguMens responsible for the development of a CAD package and measurement software. In 1991 the design study "40/80 GHz electronical MMIC circulators" started. Some activities have been done within the frame of Esprit II, Esprit III and BMBF DFE. Since 1993 he has been at the IMST where he dealt with the implementation of CPW elements into a CAD program. Furthermore, nonstandard measurement software for nonlinear characterization and active load pull has been developed. Since begin of 1995 he has been head of the section "Simulation and Measurement Software" at the IMST.

Johannes Borkes received his engineering degree (Dipl.-Eng.) in electrical engineering in 1989 from Duisburg University. From that time on he was working as a research assistant in the Department of Electrical Engineering at Duisburg University. After a short excurse in electromagnetic field theory, he worked on III-V Semiconductor design. 1994 he joined the Institute of Mobile and Satellite Communication Techniques in Kamp-Linfort, Germany, where he worked on Microsystems techniques. Currently he holds the position as a head of department "Integrated Circuits and Systems". His particular interests are MMIC and RFIC design towards "System-On-Chip-Solutions" and associated measurement techniques as well as packaging of IC’s.

Ingo Wolff (M ’75 – SM ’85 – F ’88) was born in Kösin, Germany, in 1938. He studied electrical engineering at the Technical University of Aachen and received the Dipl.-Ing. degree in 1964. In 1967 he received the doctoral degree and in 1970 the habilitation degree, also from the Technical University of Aachen, Germany. From 1970 to 1974 he was a Lecturer and Associate Professor for high-frequency techniques in Aachen. Since 1974 he has been a Full Professor of electromagnetic field theory at the University of Duisburg, Duisburg, Germany. His main areas of research are electromagnetic field theory applied to the computer-aided design of MIC’s and MMIC’s, millimeter-wave components and circuits, and the field theory of anisotropic materials. Since 1992 he has been the director of the Institute of Mobile and Satellite Communication Techniques (IMST), Kamp-Linfort, parallel to his university position. This institute intensively works in the area of mobile communication techniques, microwave and millimeter wave communication techniques, antenna techniques and electromagnetic compatibility. Since 1999 Prof. Wolff has been director of the University of Duisburg.